


CORRECTION

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Correction: Understanding the 2D-material and substrate interaction during epitaxial growth towards successful remote epitaxy: a review

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amorphous carbon (TAC)". In consistent with the corrections in text and figure caption, Fig. 3 is also updated.

Following publication of the original article [1], the authors noticed some errors.

In Sect. 4.3, "In-situ 2D growth", and in caption of Fig. 3, the compound name "h-BN" should be changed to "BN (Boron nitride)" and "graphene" to be changed to "thin

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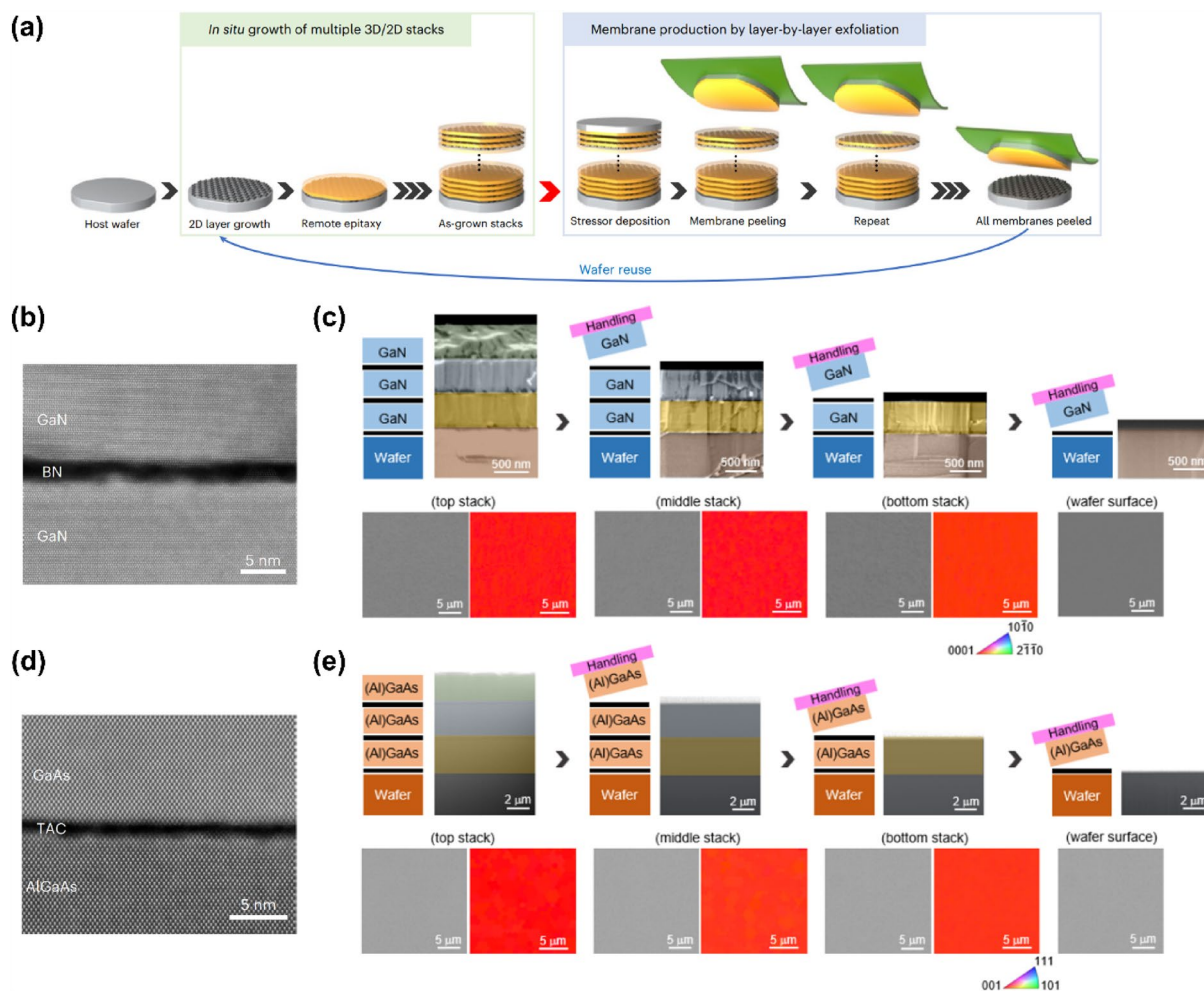


Fig. 3 Multiplication of freestanding membranes via in situ growth **a** The schematic illustration of membrane production process via in situ growth. **b** Cross-sectional TEM image of remote epitaxially grown GaN on BN/GaN. **c** False-color cross-sectional, Plan-view SEM and EBSD map of as-grown and after exfoliated GaN. **d** Cross-sectional STEM image of remote epitaxially grown GaAs on TAC/AlGaAs/GaAs. **e** False-color cross-sectional, Plan-view SEM and EBSD map of as-grown and after exfoliated GaAs. Figure reproduced from ref. [173], Springer Nature Ltd

The original article [1] has been updated.

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Reference

1. J. Ji, H.M. Kwak, J. Yu, S. Park, J.H. Park, H. Kim, S. Kim, S. Kim, D.S. Lee, H.S. Kum, Understanding the 2D-material and substrate interaction during epitaxial growth towards successful remote epitaxy: a review. *Nano Converg* **10**, 19 (2023). <https://doi.org/10.1186/s40580-023-00368-4>

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